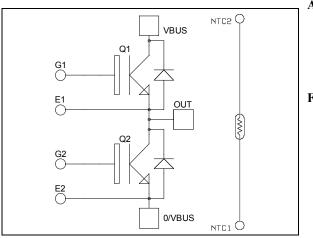
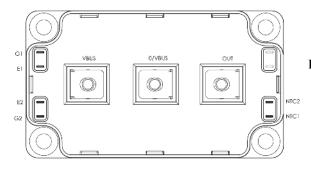


Phase leg High speed Trench + Field Stop IGBT4 Power module





APTGLQ600A65T6G

$V_{CES} = 650V$ $I_{C} = 600A^{*}$ @ Tc = 60°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- High speed Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - RBSOA and SCSOA rated
- Kelvin source for easy drive
- Very low stray inductance
- M5 power connectors
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Voltage		650	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	770*	
I _C	Continuous Conector Current	$T_C = 60^{\circ}C$	600*	Α
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	1500	
V _{GE}	Gate – Emitter Voltage		±20	V
P _D	Maximum Power Dissipation	$T_C = 25^{\circ}C$	2000	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	1200A @ 600V	

* Specification of device but current must be limited due to size of power connectors.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				600	μA
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.85	2.3	V
V _{CE(sat)}		$I_{\rm C} = 600 {\rm A}$ $T_{\rm j} = 150$	$T_{j} = 150^{\circ}C$		2.2		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 3.2 \text{ mA}$		4.2	5.1	5.6	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				1	μA

Dynamic Characteristics (per IGBT)

•	Characteristic	Test Conditions	Min	Тур	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$			36.6		
C _{oes}	Output Capacitance	$V_{CE} = 25V$			1.3		nF
C _{res}	Reverse Transfer Capacitance	f = 1 MHz		1.08			
Q _G	Gate charge	$V_{GE} = 15V$; V_{CE} $I_C = 600A$	E = 480V		3500		nC
T _{d(on)}	Turn-on Delay Time	Inductive Switc		19			
Tr	Rise Time	$V_{GE} = \pm 15V$			33		ns
T _{d(off)}	Turn-off Delay Time	$V_{CE} = 400V$ $I_{C} = 600A$			197		
T _f	Fall Time	$R_G = 0.6\Omega$		21			
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 400V$ $I_C = 600A$			19		ns
T _r	Rise Time				29		
T _{d(off)}	Turn-off Delay Time				227		
T _f	Fall Time	$R_G = 0.6\Omega$	$R_G = 0.6\Omega$		22		
Eon	Turn-on Switching Energy	$ \begin{array}{c} V_{GE} = \pm 15V & T_{J} = 25^{\circ}C \\ V_{CE} = 400V & T_{J} = 150^{\circ}C \end{array} $			12 14.7		mJ
E _{off}	Turn-off Switching Energy	$I_{\rm C} = 600 \text{A}$ $R_{\rm G} = 0.6 \Omega$	$T_{\rm J} = 25^{\circ}{\rm C}$ $T_{\rm J} = 150^{\circ}{\rm C}$		11.2 12		mJ
I _{sc}	Short Circuit data	$V_{GE} \leq 15V ; V_{Bu}$ $t_p \leq 10 \mu s ; T_j = 1$	= 600 V		3900		А
R _{thJC}	Junction to Case Thermal Resistance					0.075	°C/W

Diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Repetitive Reverse Voltage					650	V
I _{RM}	Reverse Leakage Current	$V_R = 650V$				300	μA
I _F	DC Forward Current		$T_c = 25^{\circ}C$		600		Α
V		$I_{\rm F} = 600 {\rm A}$	$T_j = 25^{\circ}C$		1.6	2	v
$V_{\rm F}$	Diode Forward Voltage	iode Forward Voltage $V_{GE} = 0V$	$T_{j} = 150^{\circ}C$		1.5		v
4	December December Time		$T_j = 25^{\circ}C$		125		
t _{rr}	Reverse Recovery Time	I (00)	$T_{j} = 150^{\circ}C$		220		ns
0	Reverse Recevery Charge	$I_{\rm F} = 600 {\rm A}$ $V_{\rm R} = 400 {\rm V}$	$I_F = 600A$ $V_D = 400V$ $T_j = 25^{\circ}C$	28.1			
Q _{rr}	Reverse Recovery Charge	$di/dt = 7000 \text{A}/\mu\text{s}$	$T_{j} = 150^{\circ}C$		59.3		μC
Er	Reverse Recovery Energy		$T_j = 25^{\circ}C$		6.6		mJ
μr	Reverse Receivery Energy		$T_{j} = 150^{\circ}C$		14.4		1115
R _{thJC}	Junction to Case Thermal Resista	nce				0.13	°C/W



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Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

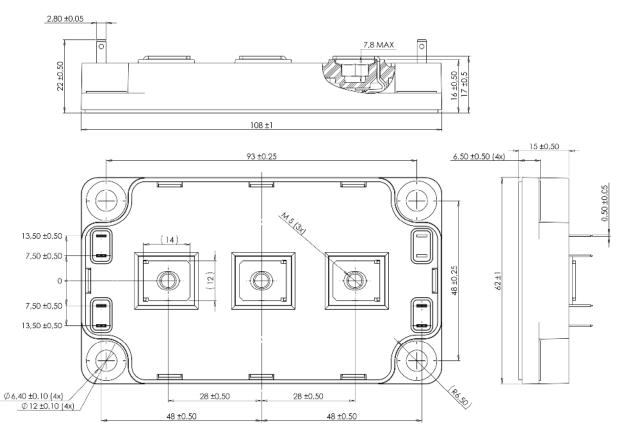
Symbol	Characteristic	,	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		T _C =100°C		4		%
	<i>P</i>					

 $R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$ T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1 \text{ min}$, 50/60Hz			4000		V
T _J	Operating junction temperature range		-40	175		
T _{JOP}	Recommended junction temperature une	der switching condition	ons	-40	T _J max -25	°C
T _{STG}	Storage Temperature Range			-40	125	C
T _C	Operating Case Temperature	-40	100			
Torque	Mounting torque	To Heatsink	M6	3	5	N.m
Torque	For teminals M5		M5	2	3.5	19.111
Wt	Package Weight				300	g

SP6 Package outline (dimensions in mm)



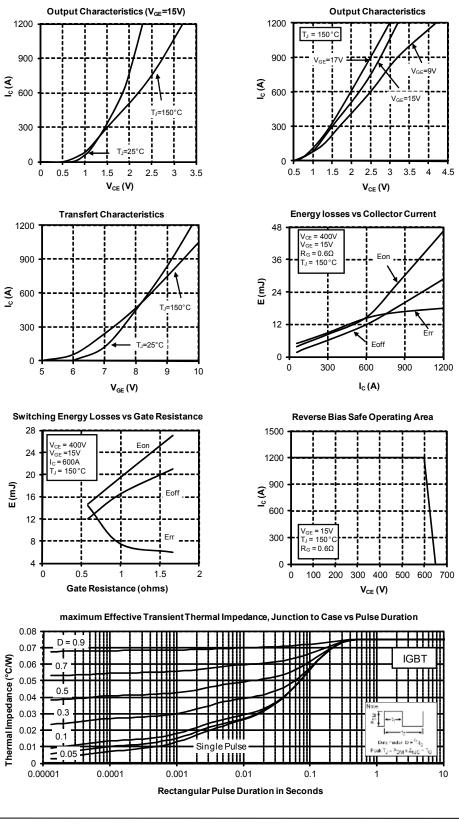
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

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Typical Performance Curve

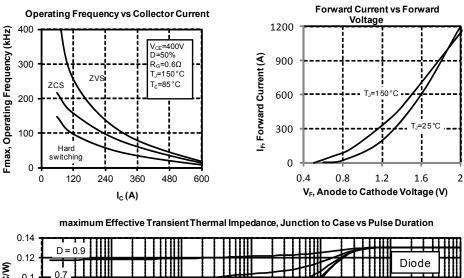


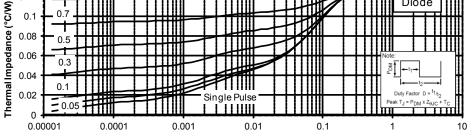
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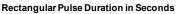
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APTGLQ600A65T6G

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